

**PATENT**

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

Serial No.: 10/797,876  
Applicant: Anthony Dip et al.  
Art Unit: 2811  
**Title: SILICON GERMANIUM SURFACE LAYER FOR HIGH-K  
DIELECTRIC INTEGRATION**  
Attorney Docket: TPS-007  
Confirmation No.: 5070

Cincinnati, Ohio 45202

June 9, 2006

Mail Stop Amendment  
Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

Sir:

**RESPONSE TO ELECTION/RESTRICTION REQUIREMENT**

This paper is responsive to the Office Action mailed May 31, 2006. The Examiner has indicated that claims 1-8, 10, 11 and 13-21 are pending in the application and are subject to restriction and/or election requirement. Specifically, we understand that the Examiner has grouped the claims between Group I, claims 1-8, 10-11 and 13-20, and Group II, claim 21. Group I is directed to a method of forming a semiconductor device, and Group II is directed to a transistor device. Applicants hereby elect Group I, claims 1-8, 10-11 and 13-20, directed to a method.

Examination on the merits of elected claims 1-8, 10-11 and 13-20 is respectfully requested.

Application Serial No. 10/797,876  
Response dated June 9, 2006  
Reply to Office Action of May 31, 2006

Respectfully submitted,

WOOD, HERRON & EVANS LLP.

By: /Kristi L. Davidson/  
Kristi L. Davidson, Reg. No. 44,643

2700 Carew Tower  
441 Vine Street  
Cincinnati, OH 45202  
513/241-2324 (voice)  
513/241-6234 (facsimile)  
K:\DEVOE\15\response to Restr Req